

Silicon NPN Power Transistors

2N6473 2N6474

DESCRIPTION

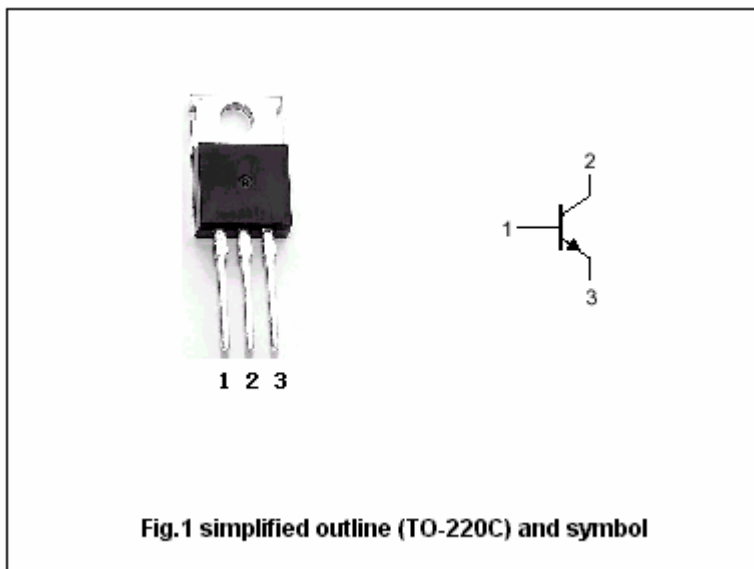
- With TO-220 package
- Low collector saturation voltage
- Excellent safe operating area

APPLICATIONS

- General-purpose medium power for switching and amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N6473	110	V
		2N6474	130	
V _{CEO}	Collector-emitter voltage	2N6473	100	V
		2N6474	120	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		4	A
I _B	Base current		2	A
P _T	Total power dissipation	T _C =25°C	40	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance from junction to case	3.125	°C/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	2N6473	I _C =0.1A ; I _B =0			V
		2N6474				
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =1.5A; I _B =0.15A			1.2	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =4A; I _B =2A			2.5	V
V _{BE-1}	Base-emitter on voltage	I _C =1.5A ; V _{CE} =4V			2.0	V
V _{BE-2}	Base-emitter on voltage	I _C =4A ; V _{CE} =2.5V			3.5	V
I _{CEx}	Collector cut-off current	2N6473	V _{CE} =100V; V _{BE} =-1.5V T _C =100 °C		0.1 2.0	mA
		2N6474				
I _{CEO}	Collector cut-off current	2N6473	V _{CE} =50V; I _B =0		1.0	mA
		2N6474				
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	mA
h _{FE-1}	DC current gain	I _C =1.5A ; V _{CE} =4V	15		150	
h _{FE-2}	DC current gain	I _C =4A ; V _{CE} =2.5V	2			
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =10V; f=1MHz			250	pF
f _T	Transition frequency	I _C =0.5A ; V _{CE} =4V	4			MHz

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PACKAGE OUTLINE

